



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



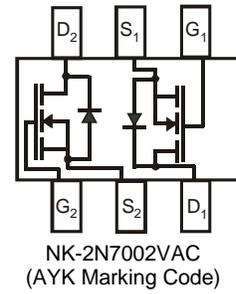
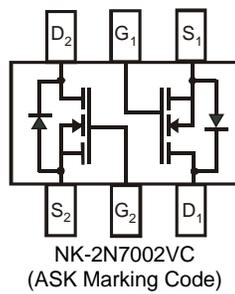
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Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram (Note 3)
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (approximate)



Maximum Ratings @ $T_A = +25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$	V_{DGR}	60	V
Gate-Source Voltage (Note 5)	Continuous	± 20	V
	Pulsed	± 40	
Drain Current (Note 5)	I_D	280	mA
Drain Current (Note 5)	I_{DM}	1.5	A

Thermal Characteristics @ $T_A = +25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation	P_D	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = +25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	70	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$ @ $T_C = +25^\circ\text{C}$ @ $T_C = +125^\circ\text{C}$
Gate-Body Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTIC (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	7.5 13.5	Ω	$V_{GS} = 5V, I_D = 0.05A,$ $V_{GS} = 10V, I_D = 0.5A, T_j = 125^\circ\text{C}$
On-State Drain Current	$I_{D(ON)}$	0.5	1.0	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	g_{FS}	80	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	—	—	20	ns	$V_{DD} = 30V, I_D = 0.2A, R_L = 150\Omega,$ $V_{GEN} = 10V, R_{GEN} = 25\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	—	20	ns	

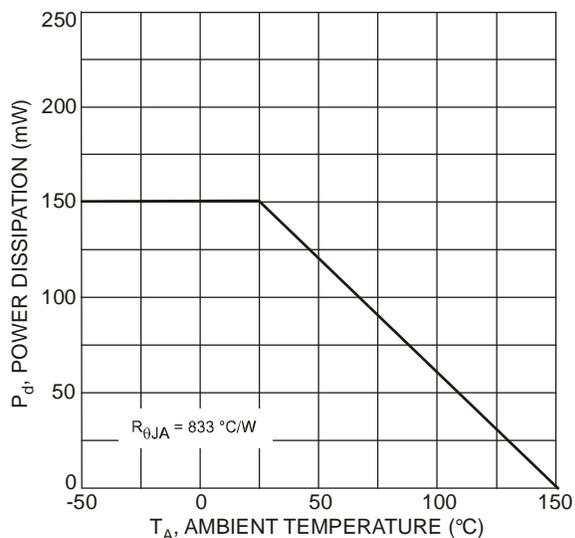
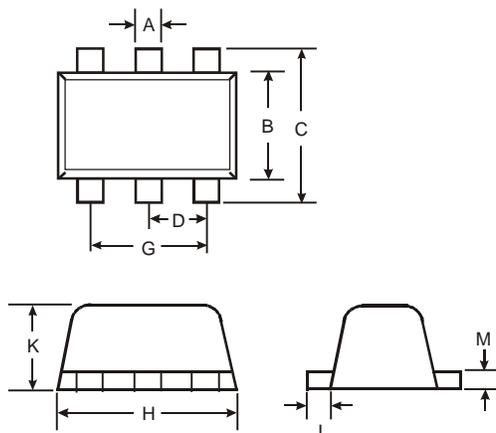


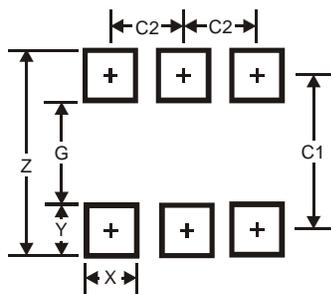
Fig. 1, Derating Curve - Total

Package Outline Dimensions



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5